



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Shunpei YAMAZAKI et al.

Serial No. 09/118,010

Filed: July 17, 1998

For: SEMICONDUCTOR DEVICE,

METHOD OF FABRICATING SAME,

AND ELECTROOPTICAL DEVICE

) Art Unit: 2822

) Examiner: M. Guerrero

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on March 17, 2003.

Adele M. Stamper

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AMENDMENT AFTER FINAL

Honorable Commissioner of Patents  
Washington, D.C. 20231

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OFFICE OF PETITIONS

Sir:

In response to the Office Action dated November 22, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

- 31
47. (Amended) A semiconductor device comprising:
- a first resinous substrate having an uneven surface, and a second resinous substrate opposed to said first resinous substrate;
  - a resinous layer provided on said uneven surface of said first resinous substrate and having a planarized surface; and
  - a thin-film transistor provided on said planarized surface of said resinous layer;
  - an interlayer insulating layer comprising a resinous material provided over said thin-film transistor; and
  - at least one pixel electrode provided on said interlayer insulating layer, wherein said thin-film transistor comprises:
    - a semiconductor layer comprising a source region, a drain region, and a channel formation region between said source region and said drain region; and

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